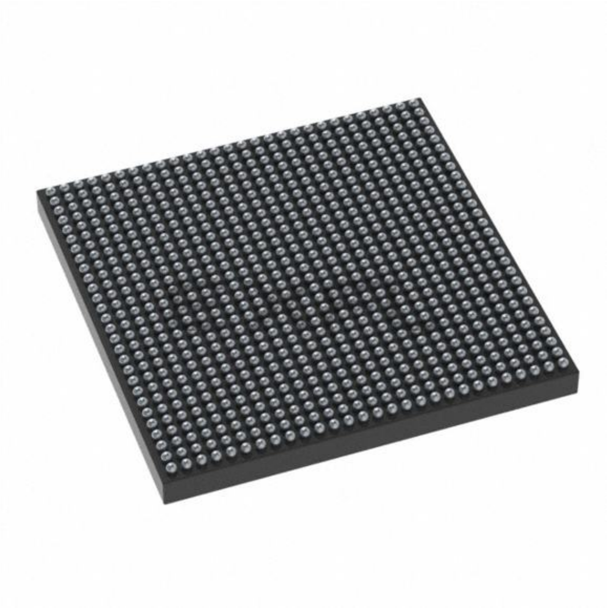

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Embedded - System On Chip (SoC): The Heart of Modern Embedded Systems

Embedded - System On Chip (SoC) refers to an integrated circuit that consolidates all the essential components of a computer system into a single chip. This includes a microprocessor, memory, and other peripherals, all packed into one compact and efficient package. SoCs are designed to provide a complete computing solution, optimizing both space and power consumption, making them ideal for a wide range of embedded applications.

What are Embedded - System On Chip (SoC)?

System On Chip (SoC) integrates multiple functions of a computer or electronic system onto a single chip. Unlike traditional multi-chip solutions, SoCs combine a central

Details	
Product Status	Active
Architecture	MCU, FPGA
Core Processor	Dual ARM® Cortex®-A53 MPCore™ with CoreSight™, Dual ARM®Cortex™-R5 with CoreSight™
Flash Size	-
RAM Size	256KB
Peripherals	DMA, WDT
Connectivity	CANbus, EBI/EMI, Ethernet, I²C, MMC/SD/SDIO, SPI, UART/USART, USB OTG
Speed	533MHz, 1.3GHz
Primary Attributes	Zynq®UltraScale+™ FPGA, 103K+ Logic Cells
Operating Temperature	0°C ~ 100°C (TJ)
Package / Case	784-BFBGA, FCBGA
Supplier Device Package	784-FCBGA (23x23)
Purchase URL	https://www.e-xfl.com/product-detail/xilinx/xczu2cg-2sfvc784e

Table 1: **Absolute Maximum Ratings[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
Video Codec Unit				
V_{CCINT_VCU}	Internal supply voltage for the video codec unit.	–0.500	1.000	V
PL System Monitor				
V_{CCADC}	PL System Monitor supply relative to GNDADC.	0.500	2.000	V
V_{REFP}	PL System Monitor reference input relative to GNDADC.	0.500	2.000	V
Temperature				
T_{STG}	Storage temperature (ambient).	–65	150	°C
T_{SOL}	Maximum soldering temperature.[12]	–	260	°C
T_j	Maximum junction temperature.[12]	–	125	°C

Notes:

1. Stresses beyond those listed under Absolute Maximum Ratings might cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those listed under Operating Conditions is not implied. Exposure to Absolute Maximum Ratings conditions for extended periods of time might affect device reliability.
2. When operating outside of the recommended operating conditions, refer to Table 6, Table 7, and Table 8 for maximum overshoot and undershoot specifications.
3. V_{CCINT_IO} must be connected to V_{CCBRAM}.
4. V_{CCAUX_IO} must be connected to V_{CCAUX}.
5. The lower absolute voltage specification always applies.
6. If V_{CCO} is 3.3V, the maximum voltage is 3.4V.
7. For I/O operation, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
8. AC coupled operation is not supported for RX termination = floating.
9. For GTY transceivers, DC coupled operation is not supported for RX termination = GND.
10. DC coupled operation is not supported for RX termination = programmable.
11. For more information on supported GTH or GTY transceiver terminations see the *UltraScale Architecture GTH Transceiver User Guide* (UG576) or *UltraScale Architecture GTY Transceiver User Guide* (UG578).
12. For soldering guidelines and thermal considerations, see the *Zynq UltraScale+ MPSoC Packaging and Pinout Specifications* (UG1075).

Available Speed Grades and Operating Voltages

Table 3 describes the speed grades per device and the V_{CCINT} operating supply voltages for the full-power, low-power, and DDR domains. For more information on selecting devices and speed grades, see the *UltraScale Architecture and Product Overview* (DS890).

Table 3: **Available Speed Grades and Operating Voltages**

Speed Grade	V_{CCINT}	$V_{CC\_PSINTLP}$	$V_{CC\_PSINTFP}$	$V_{CC\_PSINTFP\_DDR}$	Units
-3E	0.90	0.90	0.90	0.90	V
-2E	0.85	0.85	0.85	0.85	V
-2I	0.85	0.85	0.85	0.85	V
-2LE	0.85	0.85	0.85	0.85	V
-1E	0.85	0.85	0.85	0.85	V
-1I	0.85	0.85	0.85	0.85	V
-1LI	0.85	0.85	0.85	0.85	V
-2LE	0.72	0.85	0.85	0.85	V
-1LI	0.72	0.85	0.85	0.85	V

DC Characteristics Over Recommended Operating Conditions

Table 4: **DC Characteristics Over Recommended Operating Conditions**

Symbol	Description	Min	Typ[(1)]	Max	Units
V_{DRINT}	Data retention V_{CCINT} voltage (below which configuration data might be lost).	0.68	–	–	V
V_{DRAUX}	Data retention V_{CCAUX} voltage (below which configuration data might be lost).	1.5	–	–	V
I_{REF}	V_{REF} leakage current per pin.	–	–	15	µA
I_L	Input or output leakage current per pin (sample-tested).[(2)]	–	–	15	µA
C_{IN}[(3)]	Die input capacitance at the pad (HP I/O).	–	–	3.1	pF
	Die input capacitance at the pad (HD I/O).	–	–	4.75	pF
I_{RPU}	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 3.3V.	75	–	190	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 2.5V.	50	–	169	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.8V.	60	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.5V.	30	–	120	µA
	Pad pull-up (when selected) at V_{IN} = 0V, V_{CCO} = 1.2V.	10	–	100	µA
I_{RPD}	Pad pull-down (when selected) at V_{IN} = 3.3V.	60	–	200	µA
	Pad pull-down (when selected) at V_{IN} = 1.8V.	29	–	120	µA
$I_{CCADCONPL}$	Analog supply current for the PL SYSMON circuits in the power-up state.	–	–	8	mA
$I_{CCADCONPS}$	Analog supply current for the PS SYSMON circuits in the power-up state.	–	–	10	mA
$I_{CCADCOFFPL}$	Analog supply current for the PL SYSMON circuits in the power-down state.	–	–	1.5	mA
$I_{CCADCOFFPS}$	Analog supply current for the PS SYSMON circuits in the power-down state.	–	–	1.8	mA

Table 9: **Typical Quiescent Supply Current[1][2][3][4] *(Cont'd)***

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
I_{CCAUX_IOQ}	Quiescent V_{CCAUX_IO} supply current.	XCZU2	N/A	26	26	26	26	mA
		XCZU3	N/A	26	26	26	26	mA
		XCZU4	32	32	32	32	32	mA
		XCZU5	32	32	32	32	32	mA
		XCZU6	33	33	33	33	33	mA
		XCZU7	56	56	56	56	56	mA
		XCZU9	33	33	33	33	33	mA
		XCZU11	56	56	56	56	56	mA
		XCZU15	33	33	33	33	33	mA
		XCZU17	74	74	74	74	74	mA
		XCZU19	74	74	74	74	74	mA
$I_{CCBRAMQ}$	Quiescent V_{CCBRAM} supply current.	XCZU2	N/A	6	6	6	6	mA
		XCZU3	N/A	6	6	6	6	mA
		XCZU4	9	9	9	9	9	mA
		XCZU5	9	9	9	9	9	mA
		XCZU6	25	24	24	24	24	mA
		XCZU7	16	15	15	15	15	mA
		XCZU9	25	24	24	24	24	mA
		XCZU11	23	22	22	22	22	mA
		XCZU15	29	28	28	28	28	mA
		XCZU17	37	35	35	35	35	mA
		XCZU19	37	35	35	35	35	mA

Notes:

1. Typical values are specified at nominal voltage, 85°C junction temperatures (T_j) with single-ended SelectIO™ resources.
2. Typical values are for blank configured devices with no output current loads, no active input pull-up resistors, all I/O pins are 3-state and floating.
3. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate static power consumption for conditions or supplies other than those specified.
4. Typical values depend upon your configuration. To accurately estimate all PS supply currents, use the interactive XPE spreadsheet tool.

PS-PL Power Sequencing

The PS and PL power supplies are fully independent. All PS power supplies can be powered before or after any PL power supplies. The PS and PL power regions are isolated to prevent damage.

Power Supply Requirements

Table 10 shows the minimum current, in addition to I_{CCQ} maximum, required by each Zynq UltraScale+ device for proper power-on and configuration. If the current minimums shown in Table 10 are met, the device powers on after all supplies have passed through their power-on reset threshold voltages. The device must not be configured until after V_{CCINT} is applied. Once initialized and configured, use the Xilinx Power Estimator (XPE) tools to estimate current drain on these supplies.

Table 10: **Power-on Current by Device**[(1)]

I_{CC} Min =	I_{CCQ} +	XCZU2	XCZU3	XCZU4	XCZU5	XCZU6	XCZU7	XCZU9	XCZU11	XCZU15	XCZU17	XCZU19	Units
$I_{CCINTMIN}$	I_{CCINTQ} +	464	464	770	770	1800	1514	1800	1961	2242	3433	3433	mA
I_{CCINT_IOMIN} + $I_{CCBRAMMIN}$	$I_{CCBRAMQ}$ + I_{CCINT_IOQ} +	155	155	257	257	600	505	600	654	748	1145	1145	mA
I_{CCOMIN}	I_{CCOQ} +	50	50	50	50	50	50	50	55	63	96	96	mA
$I_{CCAUXMIN}$ + I_{CCAUX_IOMIN}	I_{CCAUXQ} + I_{CCAUX_IOQ} +	111	111	386	386	650	362	650	709	810	1240	1240	mA

Notes:

1. Use the Xilinx Power Estimator (XPE) spreadsheet tool (download at www.xilinx.com/power) to estimate power-on current for all supplies.

Table 11 shows the power supply ramp time.

Table 11: **Power Supply Ramp Time**

Symbol	Description	Min	Max	Units
T_{VCCINT}	Ramp time from GND to 95% of V_{CCINT}.	0.2	40	ms
T_{VCCINT_IO}	Ramp time from GND to 95% of V_{CCINT_IO}.	0.2	40	ms
T_{VCCINT_VCU}	Ramp time from GND to 95% of V_{CCINT_VCU}.	0.2	40	ms
T_{VCCO}	Ramp time from GND to 95% of V_{CCO}.	0.2	40	ms
T_{VCCAUX}	Ramp time from GND to 95% of V_{CCAUX}.	0.2	40	ms
$T_{VCCBRAM}$	Ramp time from GND to 95% of V_{CCBRAM}.	0.2	40	ms
$T_{MGTAVCC}$	Ramp time from GND to 95% of $V_{MGTAVCC}$.	0.2	40	ms
$T_{MGTAVTT}$	Ramp time from GND to 95% of $V_{MGTAVTT}$.	0.2	40	ms
$T_{MGTVCCAUX}$	Ramp time from GND to 95% of $V_{MGTVCCAUX}$.	0.2	40	ms
$T_{VCC\_PSINTFP}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP}$.	0.2	40	ms
$T_{VCC\_PSINTLP}$	Ramp time from GND to 95% of $V_{CC\_PSINTLP}$.	0.2	40	ms
T_{VCC_PSAUX}	Ramp time from GND to 95% of V_{CC_PSAUX}.	0.2	40	ms
$T_{VCC\_PSINTFP\_DDR}$	Ramp time from GND to 95% of $V_{CC\_PSINTFP\_DDR}$.	0.2	40	ms
T_{VCC_PSADC}	Ramp time from GND to 95% of V_{CC_PSADC}.	0.2	40	ms
T_{VCC_PSPLL}	Ramp time from GND to 95% of V_{CC_PSPLL}.	0.2	40	ms
$T_{PS\_MGTRAVCC}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVCC}$.	0.2	40	ms
$T_{PS\_MGTRAVTT}$	Ramp time from GND to 95% of $V_{CC\_MGTRAVTT}$.	0.2	40	ms

PL I/O Levels

Table 14: **SelectIO DC Input and Output Levels For HD I/O Banks**[(1)(2)(3)]

I/O Standard	V_{IL}		V_{IH}		V_{OL}	V_{OH}	I_{OL}	I_{OH}
	V, Min	V, Max	V, Min	V, Max	V, Max	V, Min	mA	mA
HSTL_I	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSTL_I_18	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	8.0	–8.0
HSUL_12	–0.300	V_{REF} – 0.130	V_{REF} + 0.130	V_{CCO} + 0.300	20% V_{CCO}	80% V_{CCO}	0.1	–0.1
LVCMOS12	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 4	Note 4
LVCMOS15	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS18	–0.300	35% V_{CCO}	65% V_{CCO}	V_{CCO} + 0.300	0.450	V_{CCO} – 0.450	Note 5	Note 5
LVCMOS25	–0.300	0.700	1.700	V_{CCO} + 0.300	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVCMOS33	–0.300	0.800	2.000	3.400	0.400	V_{CCO} – 0.400	Note 5	Note 5
LVTTL	–0.300	0.800	2.000	3.400	0.400	2.400	Note 5	Note 5
SSTL12	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	14.25	–14.25
SSTL135	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	8.9	–8.9
SSTL135_II	–0.300	V_{REF} – 0.090	V_{REF} + 0.090	V_{CCO} + 0.300	V_{CCO}/2 – 0.150	V_{CCO}/2 + 0.150	13.0	–13.0
SSTL15	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	8.9	–8.9
SSTL15_II	–0.300	V_{REF} – 0.100	V_{REF} + 0.100	V_{CCO} + 0.300	V_{CCO}/2 – 0.175	V_{CCO}/2 + 0.175	13.0	–13.0
SSTL18_I	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.470	V_{CCO}/2 + 0.470	8.0	–8.0
SSTL18_II	–0.300	V_{REF} – 0.125	V_{REF} + 0.125	V_{CCO} + 0.300	V_{CCO}/2 – 0.600	V_{CCO}/2 + 0.600	13.4	–13.4
MIPI_DPHY_DCI_LP[(6)]	–0.300	0.550	0.880	V_{CCO} + 0.300	0.050	1.100	0.01	–0.01

Notes:

1. Tested according to relevant specifications.
2. Standards specified using the default I/O standard configuration. For details, see the *UltraScale Architecture SelectIO Resources User Guide* (UG571).
3. POD10 and POD12 DC input and output levels are shown in Table 16, Table 20, Table 21, and Table 22.
4. Supported drive strengths of 4, 8, or 12 mA in HD I/O banks.
5. Supported drive strengths of 4, 8, 12, or 16 mA in HD I/O banks.
6. Low-power option for MIPI_DPHY_DCI.

LVDS DC Specifications (LVDS_25)

The LVDS_25 standard is available in the HD I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 23: **LVDS_25 DC Specifications**

Symbol	DC Parameter	Min	Typ	Max	Units
V_{CCO} (1)	Supply voltage.	2.375	2.500	2.625	V
V_{IDIFF}	Differential input voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High	100	350	600 (2)	mV
V_{ICM}	Input common-mode voltage.	0.300	1.200	1.425	V

Notes:

1. LVDS_25 in HD I/O banks supports inputs only. LVDS_25 inputs without internal termination have no V_{CCO} requirements. Any V_{CCO} can be chosen as long as the input voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.

LVDS DC Specifications (LVDS)

The LVDS standard is available in the HP I/O banks. See the *UltraScale Architecture SelectIO Resources User Guide* (UG571) for more information.

Table 24: **LVDS DC Specifications**

Symbol	DC Parameter	Conditions	Min	Typ	Max	Units
V_{CCO} (1)	Supply voltage.		1.710	1.800	1.890	V
V_{ODIFF} (2)	Differential output voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High	R_T = 100Ω across Q and $\overline{Q}$ signals	247	350	454	mV
V_{OCM} (2)	Output common-mode voltage.	R_T = 100 Ω across Q and $\overline{Q}$ signals	1.000	1.250	1.425	V
V_{IDIFF} (3)	Differential input voltage: $(Q - \overline{Q})$, Q = High $(\overline{Q} - Q)$, $\overline{Q}$ = High		100	350	600 (3)	mV
V_{ICM_DC} (4)	Input common-mode voltage (DC coupling).		0.300	1.200	1.425	V
V_{ICM_AC} (5)	Input common-mode voltage (AC coupling).		0.600	–	1.100	V

Notes:

1. In HP I/O banks, when LVDS is used with input-only functionality, it can be placed in a bank where the V_{CCO} levels are different from the specified level only if internal differential termination is not used. In this scenario, V_{CCO} must be chosen to ensure the input pin voltage levels do not violate the *Recommended Operating Condition* (Table 2) specification for the V_{IN} I/O pin voltage.
2. V_{OCM} and V_{ODIFF} values are for LVDS_PRE_EMPHASIS = FALSE.
3. Maximum V_{IDIFF} value is specified for the maximum V_{ICM} specification. With a lower V_{ICM}, a higher V_{DIFF} is tolerated only when the recommended operating conditions and overshoot/undershoot V_{IN} specifications are maintained.
4. Input common mode voltage for DC coupled configurations. EQUALIZATION = EQ_NONE (Default).
5. External input common mode voltage specification for AC coupled configurations. EQUALIZATION = EQ_LEVEL0, EQ_LEVEL1, EQ_LEVEL2, EQ_LEVEL3, EQ_LEVEL4.

Processor System (PS) Performance Characteristics

Table 28: **Processor Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
F_{APUMAX}	Maximum APU clock frequency.	1500	1333	1200	MHz
F_{RPUMAX}	Maximum RPU clock frequency.	600	533	500	MHz
F_{GPUMAX}	Maximum GPU clock frequency.	667	600	600	MHz

Table 29: **Configuration and Security Unit Performance**

Symbol	Description	Speed Grade			Units
		-3	-2	-1	
$F_{CSUCIBMAX}$	Maximum CSU crypto interface block frequency.	400	400	400	MHz

Table 30: **PS DDR Performance**

Memory Standard	Package	DRAM Type	Speed Grade						Units
			-3		-2		-1		
			Min	Max	Min	Max	Min	Max	
DDR4	All FFV packages, FBVB900, and SFVC784	Single rank component	664	2400	664	2400	664	2400	Mb/s
		1 rank DIMM(1)(2)	664	2133	664	2133	664	2133	Mb/s
		2 rank DIMM(1)(3)	664	1866	664	1866	664	1866	Mb/s
	SFVA625	Single rank component	664	2133	664	2133	664	2133	Mb/s
		1 rank DIMM(1)(2)	664	1866	664	1866	664	1866	Mb/s
		2 rank DIMM(1)(3)	664	1600	664	1600	664	1600	Mb/s
	SBVA484	Single rank component	664	1066	664	1066	664	1066	Mb/s
		1 rank DIMM(1)(2)	664	1066	664	1066	664	1066	Mb/s
		2 rank DIMM(1)(3)	664	1066	664	1066	664	1066	Mb/s
LPDDR4	All FFV packages, FBVB900 and SFVC784	Single die package(5)	664	2400	664	2400	664	2400	Mb/s
		Dual die package(4)(5)	664	2133	664	2133	664	2133	Mb/s
	SFVA625	Single die package(5)	664	2133	664	2133	664	2133	Mb/s
		Dual die package(4)(5)	664	1866	664	1866	664	1866	Mb/s
	SBVA484	Single die package(5)	664	1066	664	1066	664	1066	Mb/s
		Dual die package(4)(5)	664	1066	664	1066	664	1066	Mb/s

Table 31: **PS NAND NV-DDR Synchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
NV-DDR[1]	5	200	200	200	Mb/s
	4	166.6	166.6	166.6	Mb/s
	3	133.3	133.3	133.3	Mb/s
	2	100	100	100	Mb/s
	1	66.6	66.6	66.6	Mb/s
	0	40	40	40	Mb/s

Notes:

1. The PS NAND memory controller interface for NV-DDR switching characteristics meets the requirements of the ONFI 3.1 specification.

Table 32: **PS NAND SDR Asynchronous Performance**

Memory Standard	Mode	Speed Grade			Units
		-3	-2	-1	
		Max	Max	Max	
SDR[1][2]	5	50	50	50	Mb/s
	4	40	40	40	Mb/s
	3	33.3	33.3	33.3	Mb/s
	2	28.5	28.5	28.5	Mb/s
	1	20	20	20	Mb/s
	0	10	10	10	Mb/s

Notes:

1. The PS NAND memory controller interface for SDR switching characteristics meets the requirements of the ONFI 3.1 specification.
2. The NAND controller reference clock frequency maximum is 83 MHz.

Table 33: **PS-PL Interface Performance**

Symbol	Description	Min	Max	Units
$F_{EMIOGEMCLK}$	EMIO gigabit Ethernet controller maximum frequency.	–	125	MHz
$F_{EMIOSDCLK}$	EMIO SD controller maximum frequency.	–	25	MHz
$F_{EMIOSPICLK}$	EMIO SPI controller maximum frequency.	–	25	MHz
$F_{EMIOTRACECLK}$	EMIO trace controller maximum frequency.	–	125	MHz
$F_{FCIDMACLK}$	Flow control interface DMA maximum frequency.	–	333	MHz
F_{AXICLK}	Maximum AXI interface performance.	–	333	MHz
$F_{DPLIVEVIDEO}$	DisplayPort controller live video interface maximum frequency.	–	300	MHz

Table 45: **SD/SDIO Interface[1] *(Cont'd)***

Symbol	Description	Min	Max	Units
$F_{SDSDRCLK2}$	SDR50 mode device clock frequency.	–	100	MHz
	SDR25 mode device clock frequency.	–	50	MHz
SD/SDIO Interface SDR12				
$T_{DCSDHSCLK3}$	SD device clock duty cycle.	40	60	%
$T_{SDSDRCKO3}$	Clock to output delay, all outputs.	1.0	36.8	ns
$T_{SDSDRDCK3}$	Input setup time, all inputs.	24.0	–	ns
$T_{SDSDRCKD3}$	Input hold time, all inputs.	1.5	–	ns
$F_{SDSDRCLK3}$	SDR12 mode device clock frequency.	–	25	MHz
SD/SDIO Interface High-Speed Mode				
$T_{DCSDHSCLK}$	SD device clock duty cycle.	47	53	%
$T_{SDHSCKO}$	Clock to output delay, all outputs.[2]	2.2	13.8	ns
$T_{SDHSDIVW}$	Input valid data window.[3]	0.35	–	UI
$F_{SDHSCLK}$	High-speed mode SD device clock frequency.	–	50	MHz
SD/SDIO Interface Standard Mode				
$T_{DCSDSCLK}$	SD device clock duty cycle.	45	55	%
T_{SDSCKO}	Clock to output delay, all outputs.	–2.0	4.5	ns
T_{SDSDCK}	Input setup time, all inputs.	2.0	–	ns
T_{SDSCKD}	Input hold time, all inputs.	2.0	–	ns
$F_{SDIDCLK}$	Clock frequency in identification mode.	–	400	KHz
F_{SDSCLK}	Standard SD device clock frequency.	–	19	MHz

Notes:

1. The test conditions SD/SDIO standard mode (default speed mode) use an 8 mA drive strength, fast slew rate, and a 30 pF load. For SD/SDIO high-speed mode, the test conditions use a 12 mA drive strength, fast slew rate, and a 30 pF load. For other SD/SDIO modes, the test conditions use a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. This specification is achieved using pre-determined DLL tuning.
3. This specification is required for capturing input data using DLL tuning.

PS eMMC Standard Interface

Table 46: **eMMC Standard Interface[(1)]**

Symbol	Description	Min	Max	Units
eMMC Standard Interface				
$T_{DCEMMCHSCLK}$	eMMC clock duty cycle.	45	55	%
$T_{EMMCHSCKO}$	Clock to output delay, all outputs.	–2.0	4.5	ns
$T_{EMMCHSDCK}$	Input setup time, all inputs.	2.0	–	ns
$T_{EMMCHSCKD}$	Input hold time, all inputs.	2.0	–	ns
$F_{EMMCHSCLK}$	eMMC clock frequency.	–	25	MHz
eMMC High-Speed SDR Interface				
$T_{DCEMMCHSCLK}$	eMMC high-speed SDR clock duty cycle.	45	55	%
$T_{EMMCHSCKO}$	Clock to output delay, all outputs.[(2)]	3.2	16.8	ns
$T_{EMMCHSDIVW}$	Input valid data window.[(3)]	0.4	–	UI
$F_{EMMCHSCLK}$	eMMC high speed SDR clock frequency.	–	50	MHz
eMMC High-Speed DDR Interface				
$T_{DCEMMCDDRCLK}$	eMMC high-speed DDR clock duty cycle.	45	55	%
$T_{EMMCDDRSCKO1}$	Data clock to output delay.[(2)]	2.7	7.3	ns
$T_{EMMCSDRIVW}$	Input valid data window.[(3)]	3.5	–	ns
$T_{EMMCDDRSCKO2}$	Command clock to output delay.	3.2	16	ns
$T_{EMMCDDRDCK2}$	Command input setup time.	3.9	–	ns
$T_{EMMCDDRCKD2}$	Command input hold time.	2.5	–	ns
$F_{EMMCDDRCLK}$	eMMC high-speed DDR clock frequency.	–	50	MHz
eMMC HS200 Interface				
$T_{DCEMMCHS200CLK}$	eMMC HS200 clock duty cycle.	40	60	%
$T_{EMMCHS200CKO}$	Clock to output delay, all outputs.[(2)]	1.0	3.4	ns
$T_{EMMCSDR1IVW}$	Input valid data window.[(3)]	0.4	–	UI
$F_{EMMCHS200CLK}$	eMMC HS200 clock frequency.	–	200	MHz

Notes:

1. The test conditions for eMMC standard mode use an 8 mA drive strength, fast slew rate, and a 30 pF load. For eMMC high-speed mode, the test conditions use a 12 mA drive strength, fast slew rate, and a 30 pF load. For other eMMC modes, the test conditions use a 12 mA drive strength, fast slew rate, and a 15 pF load.
2. This specification is achieved using pre-determined DLL tuning.
3. This specification is required for capturing input data using DLL tuning.

Programmable Logic (PL) Performance Characteristics

This section provides the performance characteristics of some common functions and designs implemented in Zynq UltraScale+ MPSoC. These values are subject to the same guidelines as the AC Switching Characteristics, page 22. In each table, the I/O bank type is either high performance (HP) or high density (HD).

Table 70: **LVDS Component Mode Performance**

Description	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
		0.90V		0.85V				0.72V				
		-3		-2		-1		-2		-1		
		Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (OSERDES 4:1, 8:1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS TX SDR (OSERDES 2:1, 4:1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX DDR (ISERDES 1:4, 1:8)(1)	HP	0	1250	0	1250	0	1250	0	1250	0	1250	Mb/s
LVDS RX DDR	HD	0	250	0	250	0	250	0	250	0	250	Mb/s
LVDS RX SDR (ISERDES 1:2, 1:4)(1)	HP	0	625	0	625	0	625	0	625	0	625	Mb/s
LVDS RX SDR	HD	0	125	0	125	0	125	0	125	0	125	Mb/s

Notes:

1. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Table 71: **LVDS Native Mode Performance(1)(2)**

Description	DATA_WIDTH	I/O Bank Type	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3(3)		-2(3)		-1		-2(3)		-1		
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
LVDS TX DDR (TX_BITSLICE)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS TX SDR (TX_BITSLICE)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s
LVDS RX DDR (RX_BITSLICE)(4)	4	HP	375	1600	375	1600	375	1260	375	1400	375	1260	Mb/s
	8		375	1600	375	1600	375	1260	375	1600	375	1260	Mb/s
LVDS RX SDR (RX_BITSLICE)(4)	4	HP	187.5	800	187.5	800	187.5	630	187.5	700	187.5	630	Mb/s
	8		187.5	800	187.5	800	187.5	630	187.5	800	187.5	630	Mb/s

Notes:

1. Native mode is supported through the High-Speed SelectIO Interface Wizard available with the Vivado Design Suite. The performance values assume a source-synchronous interface.
2. PLL settings can restrict the minimum allowable data rate. For example, when using the PLL with CLKOUTPHY_MODE = VCO_HALF the minimum frequency is $PLL\_F_{VCOMIN}/2$.
3. In the SBVA484 package, the maximum data rate is 1260 Mb/s for DDR interfaces and 630 Mb/s for SDR interfaces.
4. LVDS receivers are typically bounded with certain applications to achieve maximum performance. Package skews are not included and should be removed through PCB routing.

Programmable Logic (PL) Switching Characteristics

Table 75 (high-density IOB (HD)) and Table 76 (high-performance IOB (HP)) summarizes the values of standard-specific data input delay adjustments, output delays terminating at pads (based on standard) and 3-state delays.

- $T_{INBUF\_DELAY\_PAD\_I}$ is the delay from IOB pad through the input buffer to the I-pin of an IOB pad. The delay varies depending on the capability of the SelectIO input buffer.
- $T_{OUTBUF\_DELAY\_O\_PAD}$ is the delay from the O pin to the IOB pad through the output buffer of an IOB pad. The delay varies depending on the capability of the SelectIO output buffer.
- $T_{OUTBUF\_DELAY\_TD\_PAD}$ is the delay from the T pin to the IOB pad through the output buffer of an IOB pad, when 3-state is disabled. The delay varies depending on the SelectIO capability of the output buffer. In HP I/O banks, the internal DCI termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the DCITERMDISABLE pin is used. In HD I/O banks, the on-die termination turn-on time is always faster than $T_{OUTBUF\_DELAY\_TD\_PAD}$ when the INTERMDISABLE pin is used.

IOB High Density (HD) Switching Characteristics

Table 75: **IOB High Density (HD) Switching Characteristics**

I/O Standards	$T_{INBUF\_DELAY\_PAD\_I}$					$T_{OUTBUF\_DELAY\_O\_PAD}$					$T_{OUTBUF\_DELAY\_TD\_PAD}$					Units
	0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		0.90V	0.85V		0.72V		
	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	-3	-2	-1	-2	-1	
DIFF_HSTL_I_18_F	0.978	0.978	1.058	0.978	1.058	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
DIFF_HSTL_I_18_S	0.978	0.978	1.058	0.978	1.058	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns
DIFF_HSTL_I_F	0.978	0.978	1.058	0.978	1.058	1.611	1.611	1.762	1.611	1.762	1.313	1.313	1.417	1.313	1.417	ns
DIFF_HSTL_I_S	0.978	0.978	1.058	0.978	1.058	1.798	1.798	1.913	1.798	1.913	1.630	1.630	1.780	1.630	1.780	ns
DIFF_HSUL_12_F	0.911	0.911	0.977	0.911	0.977	1.573	1.573	1.703	1.573	1.703	1.222	1.222	1.335	1.222	1.335	ns
DIFF_HSUL_12_S	0.911	0.911	0.977	0.911	0.977	1.711	1.711	1.864	1.711	1.864	1.536	1.536	1.665	1.536	1.665	ns
DIFF_SSTL12_F	0.906	0.906	0.977	0.906	0.977	1.643	1.643	1.792	1.643	1.792	1.285	1.285	1.423	1.285	1.423	ns
DIFF_SSTL12_S	0.906	0.906	0.977	0.906	0.977	1.784	1.784	1.948	1.784	1.948	1.567	1.567	1.706	1.567	1.706	ns
DIFF_SSTL135_F	0.927	0.927	0.995	0.927	0.995	1.625	1.625	1.765	1.625	1.765	1.341	1.341	1.458	1.341	1.458	ns
DIFF_SSTL135_II_F	0.927	0.927	0.995	0.927	0.995	1.623	1.623	1.770	1.623	1.770	1.325	1.325	1.470	1.325	1.470	ns
DIFF_SSTL135_II_S	0.927	0.927	0.995	0.927	0.995	1.768	1.768	1.916	1.768	1.916	1.722	1.722	1.911	1.722	1.911	ns
DIFF_SSTL135_S	0.927	0.927	0.995	0.927	0.995	1.869	1.869	2.025	1.869	2.025	1.814	1.814	1.976	1.814	1.976	ns
DIFF_SSTL15_F	0.928	0.928	1.020	0.928	1.020	1.628	1.628	1.771	1.628	1.771	1.374	1.374	1.483	1.374	1.483	ns
DIFF_SSTL15_II_F	0.928	0.928	1.020	0.928	1.020	1.622	1.622	1.778	1.622	1.778	1.356	1.356	1.442	1.356	1.442	ns
DIFF_SSTL15_II_S	0.928	0.928	1.020	0.928	1.020	1.821	1.821	1.987	1.821	1.987	1.895	1.895	2.047	1.895	2.047	ns
DIFF_SSTL15_S	0.928	0.928	1.020	0.928	1.020	1.824	1.824	1.977	1.824	1.977	1.743	1.743	1.907	1.743	1.907	ns
DIFF_SSTL18_II_F	0.961	0.961	1.038	0.961	1.038	1.729	1.729	1.880	1.729	1.880	1.377	1.377	1.492	1.377	1.492	ns
DIFF_SSTL18_II_S	0.961	0.961	1.038	0.961	1.038	1.796	1.796	1.965	1.796	1.965	1.616	1.616	1.800	1.616	1.800	ns
DIFF_SSTL18_I_F	0.961	0.961	1.038	0.961	1.038	1.609	1.609	1.755	1.609	1.755	1.220	1.220	1.313	1.220	1.313	ns
DIFF_SSTL18_I_S	0.961	0.961	1.038	0.961	1.038	1.786	1.786	1.942	1.786	1.942	1.677	1.677	1.836	1.677	1.836	ns
HSTL_I_18_F	0.947	0.947	1.021	0.947	1.021	1.574	1.574	1.718	1.574	1.718	1.160	1.160	1.271	1.160	1.271	ns
HSTL_I_18_S	0.947	0.947	1.021	0.947	1.021	1.805	1.805	1.950	1.805	1.950	1.748	1.748	1.867	1.748	1.867	ns

MMCM Switching Characteristics

Table 85: **MMCM Specification**

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{INMAX}$	Maximum input clock frequency.	1066	933	800	933	800	MHz
$MMCM\_F_{INMIN}$	Minimum input clock frequency.	10	10	10	10	10	MHz
$MMCM\_F_{INJITTER}$	Maximum input clock period jitter.	< 20% of clock input period or 1 ns Max					
$MMCM\_F_{INDUTY}$	Input duty cycle range: 10–49 MHz.	25–75					%
	Input duty cycle range: 50–199 MHz.	30–70					%
	Input duty cycle range: 200–399 MHz.	35–65					%
	Input duty cycle range: 400–499 MHz.	40–60					%
	Input duty cycle range: >500 MHz.	45–55					%
$MMCM\_F_{MIN\_PSCLK}$	Minimum dynamic phase shift clock frequency.	0.01	0.01	0.01	0.01	0.01	MHz
$MMCM\_F_{MAX\_PSCLK}$	Maximum dynamic phase shift clock frequency.	550	500	450	500	450	MHz
$MMCM\_F_{VCOMIN}$	Minimum MMCM VCO frequency.	800	800	800	800	800	MHz
$MMCM\_F_{VCOMAX}$	Maximum MMCM VCO frequency.	1600	1600	1600	1600	1600	MHz
$MMCM\_F_{BANDWIDTH}$	Low MMCM bandwidth at typical.(1)	1.00	1.00	1.00	1.00	1.00	MHz
	High MMCM bandwidth at typical.(1)	4.00	4.00	4.00	4.00	4.00	MHz
$MMCM\_T_{STATPHAOFFSET}$	Static phase offset of the MMCM outputs.(2)	0.12	0.12	0.12	0.12	0.12	ns
$MMCM\_T_{OUTJITTER}$	MMCM output jitter.	Note 3					
$MMCM\_T_{OUTDUTY}$	MMCM output clock duty cycle precision.(4)	0.165	0.20	0.20	0.20	0.20	ns
$MMCM\_T_{LOCKMAX}$	MMCM maximum lock time for $MMCM\_F_{PFDMIN}$.	100	100	100	100	100	µs
$MMCM\_F_{OUTMAX}$	MMCM maximum output frequency.	891	775	667	725	667	MHz
$MMCM\_F_{OUTMIN}$	MMCM minimum output frequency.(4)(5)	6.25	6.25	6.25	6.25	6.25	MHz
$MMCM\_T_{EXTFDVAR}$	External clock feedback variation.	< 20% of clock input period or 1 ns Max					
$MMCM\_RST_{MINPULSE}$	Minimum reset pulse width.	5.00	5.00	5.00	5.00	5.00	ns
$MMCM\_F_{PFDMAX}$	Maximum frequency at the phase frequency detector.	550	500	450	500	450	MHz
$MMCM\_F_{PFDMIN}$	Minimum frequency at the phase frequency detector.	10	10	10	10	10	MHz
$MMCM\_T_{FBDELAY}$	Maximum delay in the feedback path.	5 ns Max or one clock cycle					

Table 85: **MMCM Specification *(Cont'd)***

Symbol	Description	Speed Grade and V_{CCINT} Operating Voltages					Units
		0.90V	0.85V		0.72V		
		-3	-2	-1	-2	-1	
$MMCM\_F_{DPRCLK\_MAX}$	Maximum DRP clock frequency	250	250	250	250	250	MHz

Notes:

1. The MMCM does not filter typical spread-spectrum input clocks because they are usually far below the bandwidth filter frequencies.
2. The static offset is measured between any MMCM outputs with identical phase.
3. Values for this parameter are available in the Clocking Wizard.
4. Includes global clock buffer.
5. Calculated as F_{VCO}/128 assuming output duty cycle is 50%.

Table 88: **Global Clock Input to Output Delay Without MMCM (Far Clock Region)**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, *without* MMCM.								
T_{ICKOF_FAR}	Global clock input and output flip-flop *without* MMCM (far clock region).	XCZU2	N/A	5.27	5.68	5.80	6.13	ns
		XCZU3	N/A	5.27	5.68	5.80	6.13	ns
		XCZU4	5.07	6.06	6.61	6.23	7.10	ns
		XCZU5	5.07	6.06	6.61	6.23	7.10	ns
		XCZU6	5.38	6.49	6.97	7.14	7.59	ns
		XCZU7	5.39	6.54	7.01	7.16	7.62	ns
		XCZU9	5.38	6.49	6.97	7.14	7.59	ns
		XCZU11	6.18	7.41	8.11	7.66	8.99	ns
		XCZU15	5.38	6.49	6.96	7.19	7.71	ns
		XCZU17	6.21	7.53	8.07	8.36	8.90	ns
		XCZU19	6.21	7.53	8.07	8.36	8.90	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.

Table 89: **Global Clock Input to Output Delay With MMCM**

Symbol	Description	Device	Speed Grade and V_{CCINT} Operating Voltages					Units
			0.90V	0.85V		0.72V		
			-3	-2	-1	-2	-1	
SSTL15 Global Clock Input to Output Delay using Output Flip-Flop, Fast Slew Rate, with MMCM.								
$T_{ICKOFMMCMCC}$	Global clock input and output flip-flop *with* MMCM.	XCZU2	N/A	2.22	2.43	2.96	2.94	ns
		XCZU3	N/A	2.22	2.43	2.96	2.94	ns
		XCZU4	2.47	2.47	2.78	3.04	3.35	ns
		XCZU5	2.47	2.47	2.78	3.04	3.35	ns
		XCZU6	2.15	2.15	2.36	2.86	2.86	ns
		XCZU7	2.32	2.32	2.57	3.06	3.13	ns
		XCZU9	2.15	2.15	2.36	2.86	2.86	ns
		XCZU11	2.64	2.64	2.96	3.25	3.55	ns
		XCZU15	2.18	2.18	2.38	2.88	2.90	ns
		XCZU17	2.44	2.44	2.66	3.19	3.17	ns
		XCZU19	2.44	2.44	2.66	3.19	3.17	ns

Notes:

1. This table lists representative values where one global clock input drives one vertical clock line in each accessible column, and where all accessible I/O and CLB flip-flops are clocked by the global clock net.
2. MMCM output jitter is already included in the timing calculation.

Table 103: **GTH Transceiver Transmitter Switching Characteristics**

Symbol	Description	Condition	Min	Typ	Max	Units
F_{GTHTX}	Serial data rate range		0.500	–	F_{GTHMAX}	Gb/s
T_{RTX}	TX rise time	20%–80%	–	21	–	ps
T_{FTX}	TX fall time	80%–20%	–	21	–	ps
T_{LLSKEW}	TX lane-to-lane skew(1)		–	–	500.00	ps
$T_{J16.375}$	Total jitter(2)(4)	16.375 Gb/s	–	–	0.28	UI
$D_{J16.375}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J15.0}$	Total jitter(2)(4)	15.0 Gb/s	–	–	0.28	UI
$D_{J15.0}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.1 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J14.1}$	Total jitter(2)(4)	14.025 Gb/s	–	–	0.28	UI
$D_{J14.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J13.1}$	Total jitter(2)(4)	13.1 Gb/s	–	–	0.28	UI
$D_{J13.1}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_QPLL}$	Total jitter(2)(4)	12.5 Gb/s	–	–	0.28	UI
$D_{J12.5\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J12.5\_CPLL}$	Total jitter(3)(4)	12.5 Gb/s	–	–	0.33	UI
$D_{J12.5\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J11.3\_QPLL}$	Total jitter(2)(4)	11.3 Gb/s	–	–	0.28	UI
$D_{J11.3\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_QPLL}$	Total jitter(2)(4)	10.3125 Gb/s	–	–	0.28	UI
$D_{J10.3125\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J10.3125\_CPLL}$	Total jitter(3)(4)	10.3125 Gb/s	–	–	0.33	UI
$D_{J10.3125\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J9.953\_QPLL}$	Total jitter(2)(4)	9.953 Gb/s	–	–	0.28	UI
$D_{J9.953\_QPLL}$	Deterministic jitter(2)(4)		–	–	0.17	UI
$T_{J9.953\_CPLL}$	Total jitter(3)(4)	9.953 Gb/s	–	–	0.33	UI
$D_{J9.953\_CPLL}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J8.0}$	Total jitter(3)(4)	8.0 Gb/s	–	–	0.32	UI
$D_{J8.0}$	Deterministic jitter(3)(4)		–	–	0.17	UI
$T_{J6.6}$	Total jitter(3)(4)	6.6 Gb/s	–	–	0.30	UI
$D_{J6.6}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J5.0}$	Total jitter(3)(4)	5.0 Gb/s	–	–	0.30	UI
$D_{J5.0}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.25}$	Total jitter(3)(4)	4.25 Gb/s	–	–	0.30	UI
$D_{J4.25}$	Deterministic jitter(3)(4)		–	–	0.15	UI
$T_{J4.0}$	Total jitter(3)(4)	4.0 Gb/s	–	–	0.32	UI
$D_{J4.0}$	Deterministic jitter(3)(4)		–	–	0.16	UI
$T_{J3.20}$	Total jitter(3)(4)	3.20 Gb/s(5)	–	–	0.20	UI
$D_{J3.20}$	Deterministic jitter(3)(4)		–	–	0.10	UI

Table 104: **GTH Transceiver Receiver Switching Characteristics *(Cont'd)***

Symbol	Description	Condition	Min	Typ	Max	Units
$J_{T\_SJ2.5}$	Sinusoidal jitter (CPLL)(3)	2.5 Gb/s(5)	0.30	–	–	UI
$J_{T\_SJ1.25}$	Sinusoidal jitter (CPLL)(3)	1.25 Gb/s(6)	0.30	–	–	UI
J_{T_SJ500}	Sinusoidal jitter (CPLL)(3)	500 Mb/s(7)	0.30	–	–	UI
SJ Jitter Tolerance with Stressed Eye(2)						
$J_{T\_TJSE3.2}$	Total jitter with stressed eye(8)	3.2 Gb/s	0.70	–	–	UI
$J_{T\_TJSE6.6}$		6.6 Gb/s	0.70	–	–	UI
$J_{T\_SJSE3.2}$	Sinusoidal jitter with stressed eye(8)	3.2 Gb/s	0.10	–	–	UI
$J_{T\_SJSE6.6}$		6.6 Gb/s	0.10	–	–	UI

Notes:

1. Using RXOUT_DIV = 1, 2, and 4.
2. All jitter values are based on a bit error ratio of 10^{-12}.
3. The frequency of the injected sinusoidal jitter is 80 MHz.
4. CPLL frequency at 3.2 GHz and RXOUT_DIV = 2.
5. CPLL frequency at 2.5 GHz and RXOUT_DIV = 2.
6. CPLL frequency at 2.5 GHz and RXOUT_DIV = 4.
7. CPLL frequency at 2.0 GHz and RXOUT_DIV = 8.
8. Composite jitter with RX equalizer enabled. DFE disabled.

GTH Transceiver Electrical Compliance

The *UltraScale Architecture GTH Transceiver User Guide* (UG576) contains recommended use modes that ensure compliance for the protocols listed in Table 105. The transceiver wizard provides the recommended settings for those use cases and for protocol specific characteristics.

Table 105: **GTH Transceiver Protocol List**

Protocol	Specification	Serial Rate (Gb/s)	Electrical Compliance
CAUI-10	IEEE 802.3-2012	10.3125	Compliant
nPPI	IEEE 802.3-2012	10.3125	Compliant
10GBASE-KR(1)	IEEE 802.3-2012	10.3125	Compliant
40GBASE-KR	IEEE 802.3-2012	10.3125	Compliant
SFP+	SFF-8431 (SR and LR)	9.95328–11.10	Compliant
XFP	INF-8077i, revision 4.5	10.3125	Compliant
RXAUI	CEI-6G-SR	6.25	Compliant
XAUI	IEEE 802.3-2012	3.125	Compliant
1000BASE-X	IEEE 802.3-2012	1.25	Compliant
5.0G Ethernet	IEEE 802.3bx (PAR)	5	Compliant
2.5G Ethernet	IEEE 802.3bx (PAR)	2.5	Compliant
HiGig, HiGig+, HiGig2	IEEE 802.3-2012	3.74, 6.6	Compliant
OTU2	ITU G.8251	10.709225	Compliant
OTU4 (OTL4.10)	OIF-CEI-11G-SR	11.180997	Compliant
OC-3/12/48/192	GR-253-CORE	0.1555–9.956	Compliant
TFI-5	OIF-TFI5-0.1.0	2.488	Compliant
Interlaken	OIF-CEI-6G, OIF-CEI-11G-SR	4.25–12.5	Compliant
PCIe Gen1, 2, 3	PCI Express base 3.0	2.5, 5.0, and 8.0	Compliant
SDI(2)	SMPTE 424M-2006	0.27–2.97	Compliant
UHD-SDI(2)	SMPTE ST-2081 6G, SMPTE ST-2082 12G	6 and 12	Compliant
Hybrid memory cube (HMC)	HMC-15G-SR	10, 12.5, and 15.0	Compliant
MoSys Bandwidth Engine	CEI-11-SR and CEI-11-SR (overclocked)	10.3125, 15.5	Compliant
CPRI	CPRI_v_6_1_2014-07-01	0.6144–12.165	Compliant
HDMI(2)	HDMI 2.0	All	Compliant
Passive optical network (PON)	10G-EPON, 1G-EPON, NG-PON2, XG-PON, and 2.5G-PON	0.155–10.3125	Compliant
JESD204a/b	OIF-CEI-6G, OIF-CEI-11G	3.125–12.5	Compliant
Serial RapidIO	RapidIO specification 3.1	1.25–10.3125	Compliant
DisplayPort(2)	DP 1.2B CTS	1.62–5.4	Compliant
Fibre channel	FC-PI-4	1.0625–14.025	Compliant
SATA Gen1, 2, 3	Serial ATA revision 3.0 specification	1.5, 3.0, and 6.0	Compliant
SAS Gen1, 2, 3	T10/BSR INCITS 519	3.0, 6.0, and 12.0	Compliant
SFI-5	OIF-SFI5-01.0	0.625–12.5	Compliant
Aurora	CEI-6G, CEI-11G-LR	up to 11.180997	Compliant

Notes:

1. The transition time of the transmitter is faster than the IEEE Std 802.3-2012 specification.
2. This protocol requires external circuitry to achieve compliance.

GTY Transceiver Switching Characteristics

Consult the *UltraScale Architecture GTY Transceiver User Guide* (UG578) for further information.

Table 109: **GTY Transceiver Performance**

Symbol	Description	Output Divider	Speed Grade and V_{CCINT} Operating Voltages										Units
			0.90V		0.85V				0.72V				
			-3		-2		-1		-2		-1		
F_{GTYMAX}	GTY maximum line rate		32.75		28.21		25.7813		28.21		12.5		Gb/s
F_{GTYMIN}	GTY minimum line rate		0.5		0.5		0.5		0.5		0.5		Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYCRANGE}$	CPLL line rate range(1)	1	4.0	12.5	4.0	12.5	4.0	8.5	4.0	12.5	4.0	8.5	Gb/s
		2	2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	Gb/s
		4	1.0	3.125	1.0	3.125	1.0	2.125	1.0	3.125	1.0	2.125	Gb/s
		8	0.5	1.5625	0.5	1.5625	0.5	1.0625	0.5	1.5625	0.5	1.0625	Gb/s
		16	N/A										Gb/s
		32	N/A										Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE1}$	QPLL0 line rate range(2)	1	19.6	32.75	19.6	28.21	19.6	25.7813	19.6	28.21	N/A		Gb/s
		1	9.8	16.375	9.8	16.375	9.8	12.5	9.8	16.375	9.8	12.5	Gb/s
		2	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	4.9	8.1875	Gb/s
		4	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	2.45	4.0938	Gb/s
		8	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	1.225	2.0469	Gb/s
		16	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	0.6125	1.0234	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{GTYQRANGE2}$	QPLL1 line rate range(3)	1	16.0	26.0	16.0	26.0	19.6	25.7813	16.0	26.0	N/A		Gb/s
		1	8.0	13.0	8.0	13.0	8.0	12.5	8.0	13.0	8.0	12.5	Gb/s
		2	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	4.0	6.5	Gb/s
		4	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	2.0	3.25	Gb/s
		8	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	1.0	1.625	Gb/s
		16	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	0.5	0.8125	Gb/s
			Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
$F_{CPLLRANGE}$	CPLL frequency range		2.0	6.25	2.0	6.25	2.0	4.25	2.0	6.25	2.0	4.25	GHz
$F_{QPLL0RANGE}$	QPLL0 frequency range		9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	9.8	16.375	GHz
$F_{QPLL1RANGE}$	QPLL1 frequency range		8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	8.0	13.0	GHz

Notes:

1. The values listed are the rounded results of the calculated equation (2 x CPLL_Frequency)/Output_Divider.
2. The values listed are the rounded results of the calculated equation (2 x QPLL0_Frequency)/Output_Divider.
3. The values listed are the rounded results of the calculated equation (2 x QPLL1_Frequency)/Output_Divider.

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